



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

H. WATANABE et al.

Group Art Unit: 2825

Serial No.: 09/320,271

Examiner: C. Lee

Filed: May 27, 1999

For: **SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF**

PRELIMINARY AMENDMENT

Commission for Patents
Washington, D. C. 20231

January 28, 2002

Sir:

Prior to continued examination on the merits, please amend the above- identified application
as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

1. **(Three Times Amended)** A fabrication method of a semiconductor device
comprising the steps of:
- forming a first insulation layer over a substrate,
 - introducing impurities into said first insulation layer,
 - forming, in said first insulation layer, a trench extending in a line, and
 - embedding and forming a first conductive layer in said trench extending linearly.